

Substitute for Form 1449 A & B/PTO <u>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</u> <i>(use as many sheets as necessary)</i>				<i>Complete if Known</i>	
				Application Number	10/510,916
				Confirmation Number	7320
				Filing Date	October 12, 2004
				First Named Inventor	Shinichi ISHIBASHI
				Art Unit	2812
				Examiner Name	Not yet assigned
Sheet	1	of	1	Attorney Docket Number	Q84137

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
		US			
		US			
		US			
		US			
		US			
		US			

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ <i>(if known)</i>			

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		SHINJI TSUBOI, et al., Recent progress in 1Xx-ray mask technology: Feasibility Study using ASET-NIST format TaXN x-ray masks with 100 nm rule 4 Gbit dynamic random access memory test patterns, 2001 American Society, pgs. 2416-2422.	
		M. TAKAHASHI, et al., Smooth, low-stress, sputtered tantalum and tantalum alloy films for the absorber material of reflective-type EUVL, In Emerging Lithographic Technologies IV, Elizabeth A. Dabisz, Editor, Proceedings of SPIE Vol. 3997 (2000), pgs. 484-495.	
		KENNETH RACETTE, et al., Sputter deposition and annealing of Ta, TaSI _x and TaB _x composite films and their application in next generation lithography masks, 2000 American Vacuum Society, pgs. 1119-1124.	

Examiner Signature		Date Considered	
--------------------	--	-----------------	--